TEMIC

Siliconix

2N3958

Monolithic N-Channel JFET Dual

Product Summary

$V_{GS(off)}$ (V)	$V_{(BR)GSS}$ Min (V)	g_{fs} Min (mS)	I_G Max (pA)	$\|V_{GS1} - V_{GS2}\|$ Max (mV)
−1.0 to −4.5	−50	1	−50	25

Features

- Monolithic Design
- High Slew Rate
- Low Offset/Drift Voltage
- Low Gate Leakage: 5 pA
- Low Noise: 9 nV/√Hz
- High CMRR: 100 dB

Benefits

- Tight Differential Match vs. Current
- Improved Op Amp Speed, Settling Time Accuracy
- Minimum Input Error/Trimming Requirement
- Insignificant Signal Loss/Error Voltage
- High System Sensitivity
- Minimum Error with Large Input Signal

Applications

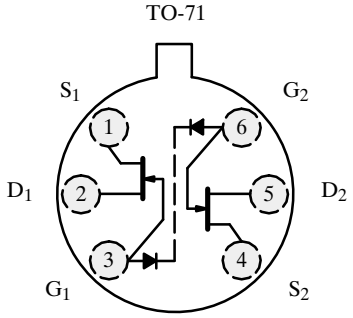
- Wideband Differential Amps
- High-Speed, Temp-Compensated, Single-Ended Input Amps
- High Speed Comparators
- Impedance Converters

Description

The low cost 2N3958 JFET dual is designed for high-performance differential amplification for a wide range of precision test instrumentation applications. This series features tightly matched specs, low gate leakage for accuracy, and wide dynamic range with I_G guaranteed at V_{DG} = 20 V.

The hermetically-sealed TO-71 package is available with full military processing (see Military Information and the 2N5545/5546/5547JANTX/JANTXV data sheet).

For similar products see 2N5196/5197/5198/5199, the low-noise U/SST401 series, the high-gain 2N5911/5912, and the low-leakage U421/423 data sheets.



Absolute Maximum Ratings

Gate-Drain, Gate-Source Voltage	−50 V
Gate Current	50 mA
Lead Temperature ($^1/_{16}$" from case for 10 sec.)	300 °C
Storage Temperature	−65 to 200°C
Operating Junction Temperature	−55 to 150°C

Power Dissipation :	Per Side[a]	250 mW
	Total[b]	500 mW

Notes
a. Derate 2 mW/°C above 85°C
b. Derate 4 mW/°C above 85°C

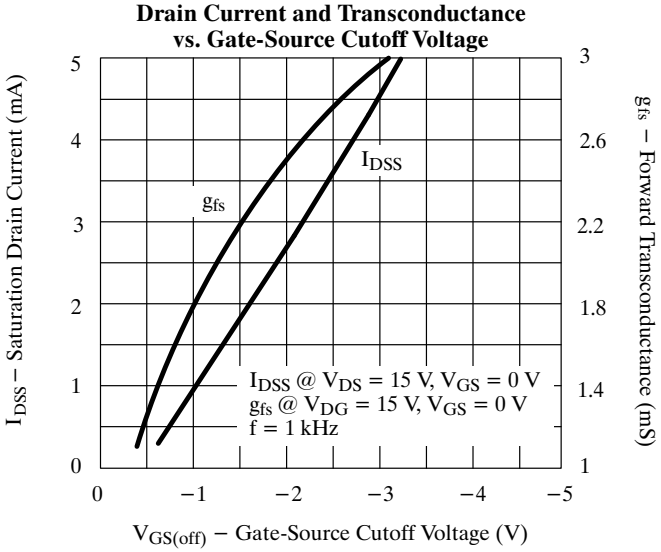
2N3958

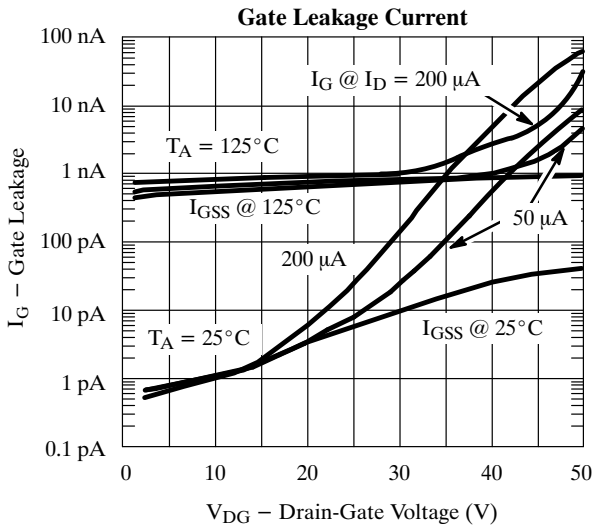
Specifications[a]

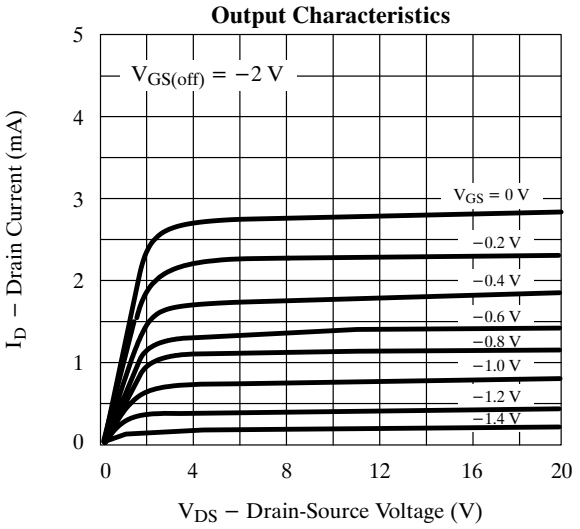
Parameter	Symbol	Test Conditions	Limits Min	Limits Typ[b]	Limits Max	Unit
Static						
Gate-Source Breakdown Voltage	$V_{(BR)GSS}$	$I_G = -1$ µA, $V_{DS} = 0$ V	−50	−57		V
Gate-Source Cutoff Voltage	$V_{GS(off)}$	$V_{DS} = 20$ V, $I_D = 1$ nA	−1.0	−2	−4.5	V
Saturation Drain Current[c]	I_{DSS}	$V_{DS} = 20$ V, $V_{GS} = 0$ V	0.5	3	5	mA
Gate Reverse Current	I_{GSS}	$V_{GS} = -30$ V, $V_{DS} = 0$ V		−10	−100	pA
		$T_A = 150°C$		−20	−500	nA
Gate Operating Current	I_G	$V_{DG} = 20$ V, $I_D = 200$ µA		−5	−50	pA
		$T_A = 125°C$		−0.8	−250	nA
Gate-Source Voltage	V_{GS}	$V_{DG} = 20$ V, $I_D = 200$ µA	−0.5	−1.5	−4	V
		$I_D = 50$ µA			−4.2	
Gate-Source Forward Voltage	$V_{GS(F)}$	$I_G = 1$ mA, $V_{DS} = 0$ V			2	
Dynamic						
Common-Source Forward Transconductance	g_{fs}	$V_{DS} = 20$ V, $V_{GS} = 0$ V, f = 1 kHz	1	2.5	3	mS
Common-Source Output Conductance	g_{os}			2	35	µS
Common-Source Input Capacitance	C_{iss}	$V_{DS} = 20$ V, $V_{GS} = 0$ V, f = 1 MHz		3	4	pF
Common-Source Reverse Transfer Capacitance	C_{rss}			1	1.2	
Drain-Gate Capacitance	C_{dg}	$V_{DG} = 10$ V, $I_S = 0$, f = 1 MHz			1.5	
Equivalent Input Noise Voltage	$\bar{e}_n$	$V_{DS} = 20$ V, $V_{GS} = 0$ V, f = 1 kHz		9		$\frac{nV}{\sqrt{Hz}}$
Noise Figure	NF	$V_{DS} = 20$ V, $V_{GS} = 0$ V, f = 100 Hz, $R_G = 10$ MΩ			0.5	dB
Matching						
Differential Gate-Source Voltage	$\lvert V_{GS1} - V_{GS2} \rvert$	$V_{DG} = 20$ V, $I_D = 200$ µA			25	mV
Gate-Source Voltage Differential Change with Temperature	$\frac{\Delta \lvert V_{GS1} - V_{GS2} \rvert}{\Delta T}$	$V_{DG} = 20$ V, $I_D = 200$ µA, $T_A = -55$ to 125°C			100	µV/°C
Saturation Drain Current Ratio	$\frac{I_{DSS1}}{I_{DSS2}}$	$V_{DS} = 20$ V, $V_{GS} = 0$ V	0.85	0.97	1	
Transconductance Ratio	$\frac{g_{fs1}}{g_{fs2}}$	$V_{DS} = 20$ V, $I_D = 200$ µA, f = 1 kHz	0.85	0.97	1	
Differential Output Conductance	$\lvert g_{os1} - g_{os2} \rvert$			0.1		µS
Differential Gate Current	$\lvert I_{G1} - I_{G2} \rvert$	$V_{DG} = 20$ V, $I_D = 200$ µA, $T_A = 125°C$		0.1	10	nA
Common Mode Rejection Ratio[d]	CMRR	$V_{DG} = 10$ to 20 V, $I_D = 200$ µA		100		dB

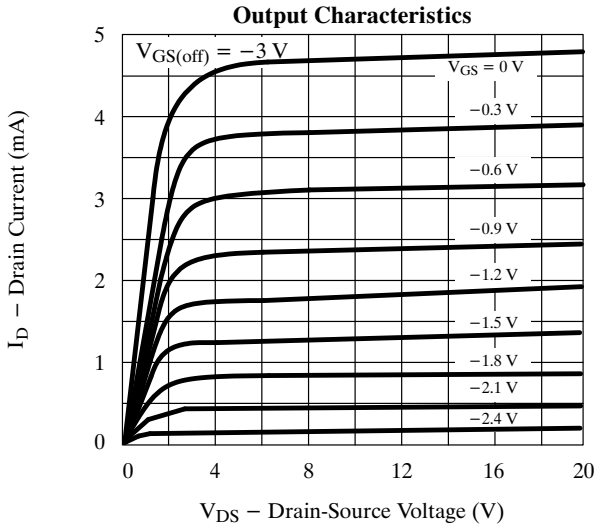
Notes
a. $T_A = 25°C$ unless otherwise noted. NQP
b. Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing.
c. Pulse test: PW ≤ 300 µs duty cycle ≤ 3%.
d. This parameter not registered with JEDEC.

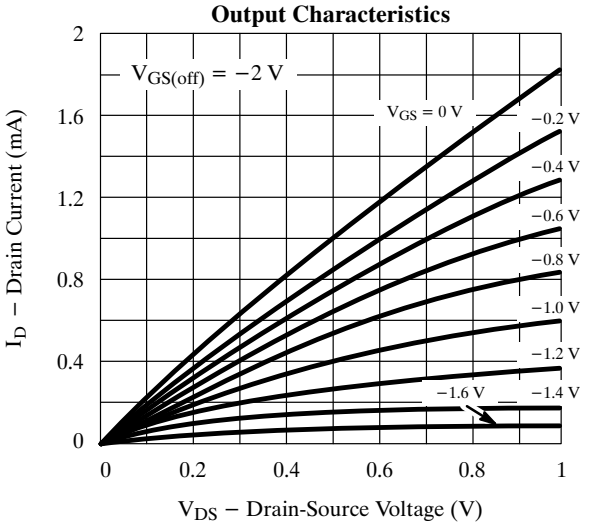
Typical Characteristics

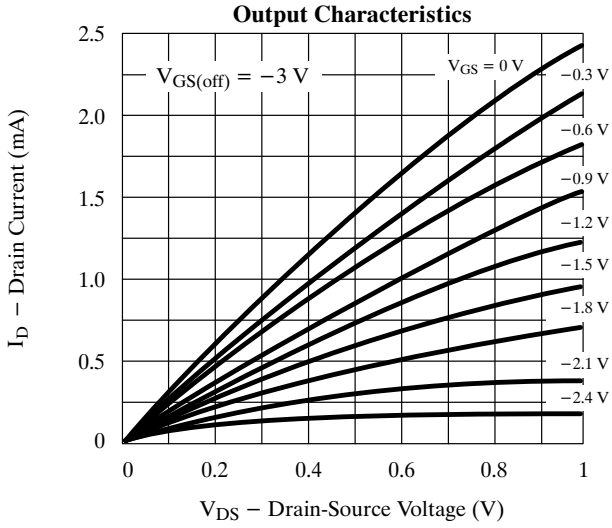








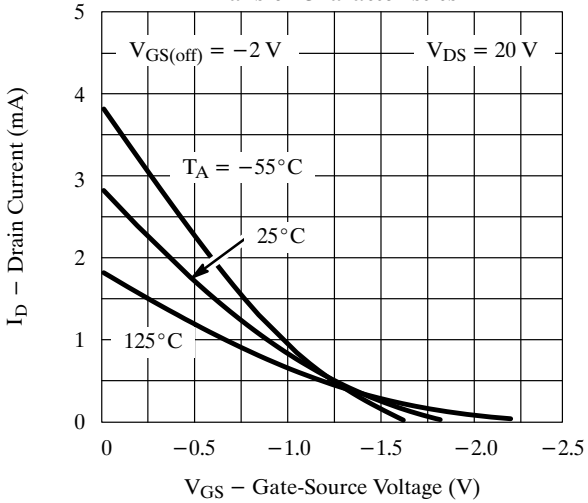




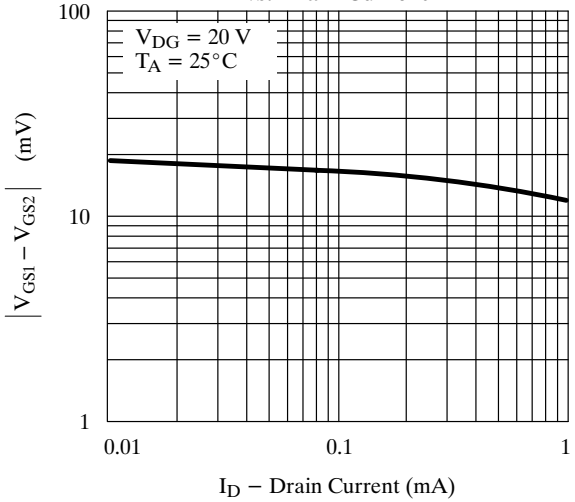
2N3958

Typical Characteristics (Cont'd)

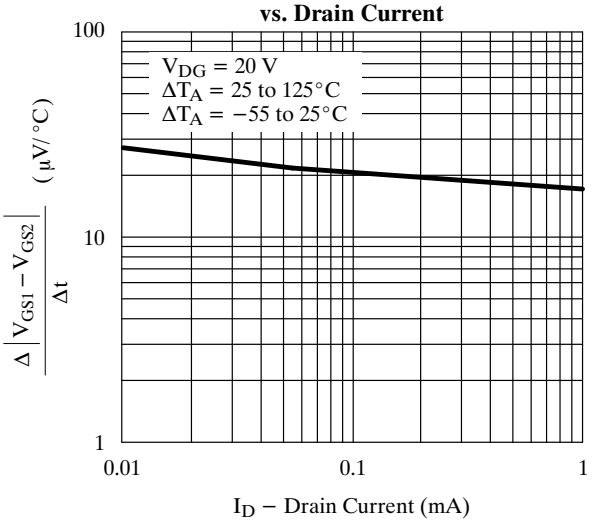
Transfer Characteristics



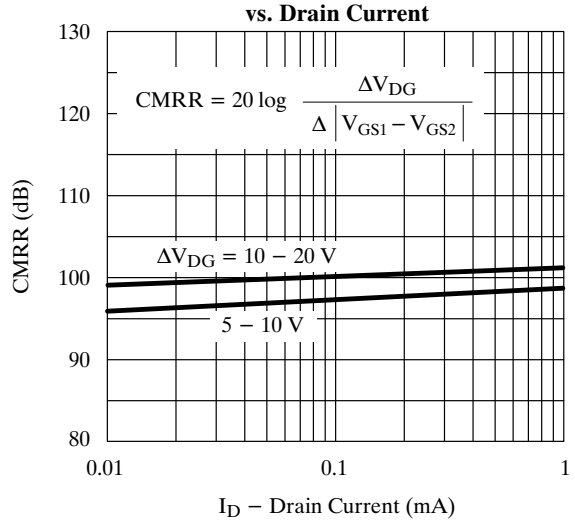
Gate-Source Differential Voltage vs. Drain Current



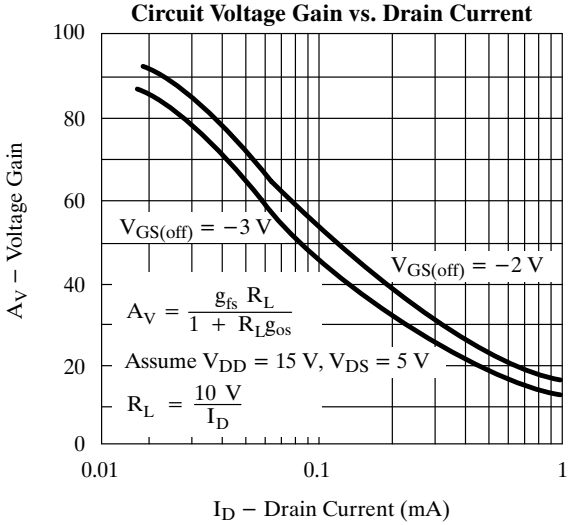
Voltage Differential with Temperature vs. Drain Current



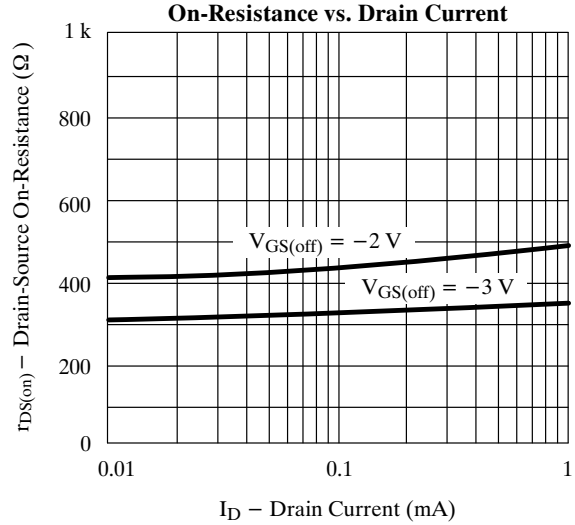
Common Mode Rejection Ratio vs. Drain Current



Circuit Voltage Gain vs. Drain Current

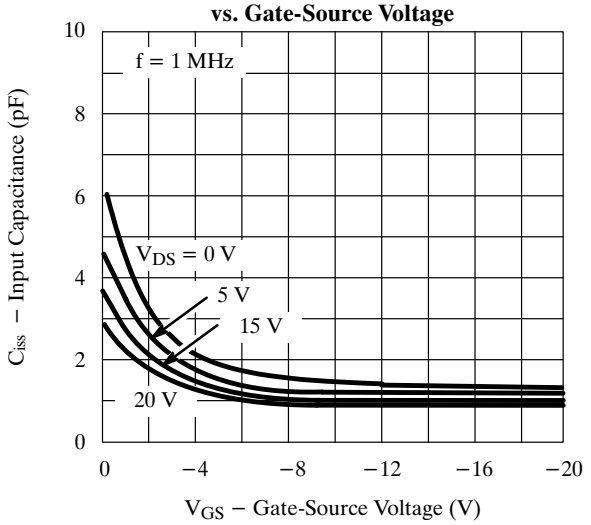


On-Resistance vs. Drain Current

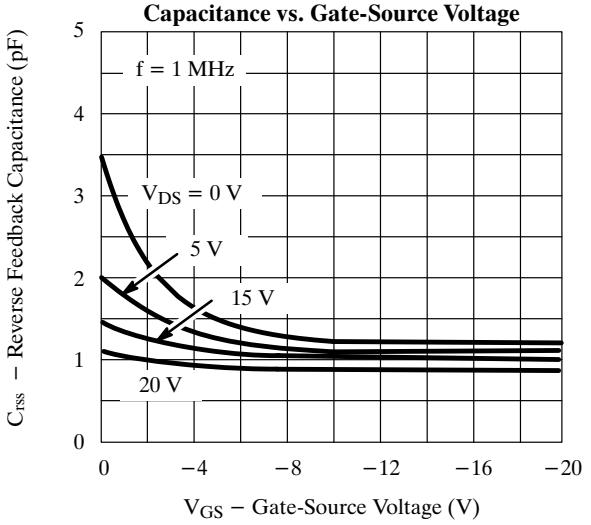


Typical Characteristics (Cont'd)

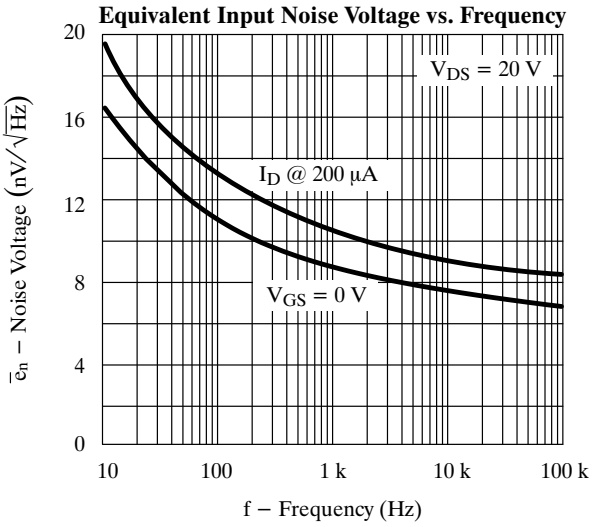
Common-Source Input Capacitance vs. Gate-Source Voltage



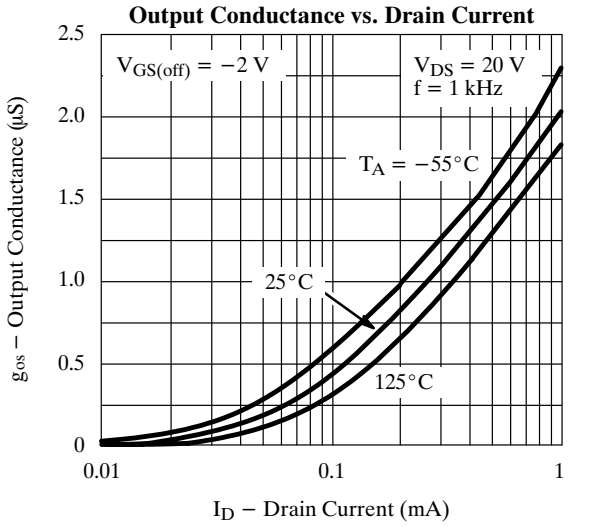
Common-Source Reverse Feedback Capacitance vs. Gate-Source Voltage



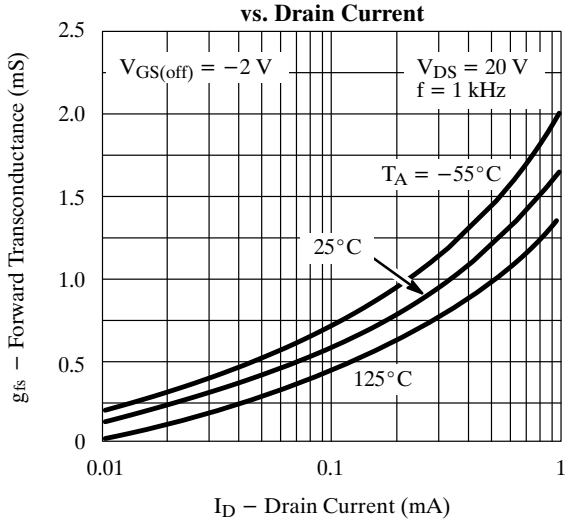
Equivalent Input Noise Voltage vs. Frequency



Output Conductance vs. Drain Current



Common-Source Forward Transconductance vs. Drain Current



On-Resistance and Output Conductance vs. Gate-Source Cutoff Voltage